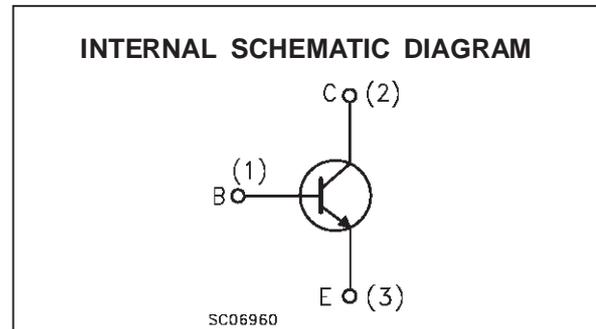
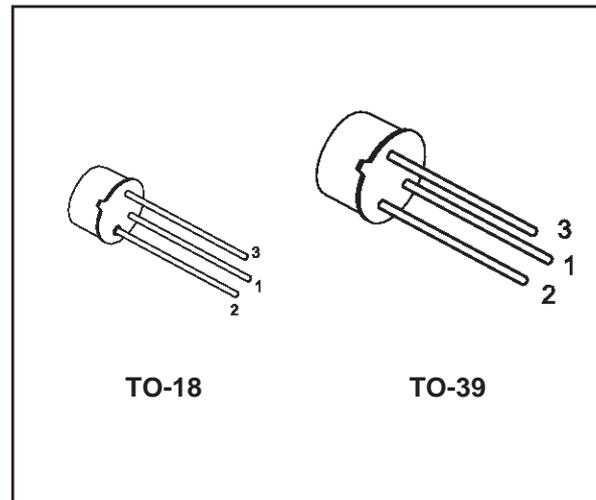


HIGH SPEED SWITCHES

DESCRIPTION

The 2N2219A and 2N2222A are silicon planar epitaxial NPN transistors in Jedec TO-39 (for 2N2219A) and in Jedec TO-18 (for 2N2222A) metal case. They are designed for high speed switching application at collector current up to 500mA, and feature useful current gain over a wide range of collector current, low leakage currents and low saturation voltage.

☞ 2N2219A approved to CECC 50002-100,
2N2222A approved to CECC 50002-101
available on request.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	75	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	40	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	6	V
I_C	Collector Current	0.8	A
P_{tot}	Total Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$ for 2N2219A for 2N2222A at $T_{case} \leq 25\text{ }^\circ\text{C}$ for 2N2219A for 2N2222A	0.8	W
		0.5	W
		3	W
		1.8	W
T_{stg}	Storage Temperature	-65 to 200	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$